

**79.** The process of claim **78** wherein forming said passivation layer comprises forming a layer of dielectric material on said second exposed area.

**80.** The process of claim **79** wherein forming said layer of dielectric material comprises forming a layer of silicon nitride or silicon dioxide on said second exposed area.

**81.** The process of claim **80** wherein forming said layer of dielectric material comprises forming a layer of dielectric material such that said layer has a thickness of about 2 nanometers or less.

\* \* \* \* \*